IN THE CLAIMS:

Please amend claims 17 and 36 as follows:

1-7. (Canceled)

8. (Previously Presented) A method for planarizing an organosilicate layer, comprising:

positioning a substrate having an organosilicate layer thereon in a polishing system;

providing a slurry including silica as an abrasive material dispersed in a solvent to the polishing system, wherein the slurry has a pH of about 10 or greater; and

polishing the organosilicate layer using the slurry.

9. (Canceled)

10. (Original) The method of claim 8 wherein the abrasive material has an average particle size greater than about 35 nm (nanometers).

11. (Previously Presented) The method of claim 8 wherein the pH of the slurry is adjusted by adding potassium hydroxide (KOH) or ammonium hydroxide (NH_4OH) thereto.

12-13. (Canceled)

14. (Previously Presented) The method of claim 8 wherein the concentration of abrasive material in the slurry is within a range of about 22% by weight to about 30% by weight.

15. (Original) The method of claim 8 wherein the organosilicate layer is polished by placing it in contact with a polishing pad, the polishing pad having the slurry thereon, and wherein the polishing pad is disposed upon a rotatable platen.

16. (Original) The method of claim 15 wherein the polishing pad comprises polyurethane.

17. (Currently Amended) The method of claim 15 wherein the organosilicate layer contacts the polishing pad with a pressure within a range of about 1 psi (pounds/square inch) to about 14 psi.

18. (Original) The method of claim 15 wherein the platen rotates at a speed within the range of about 0.1 m/s (meters/second) to about 2 m/s.

19. (Previously Presented) A method for fabricating a device, comprising:

providing a substrate having conductive features formed thereon with an organosilicate layer deposited between and on top of the conductive features;

positioning the substrate in a polishing system;

providing a slurry including silica as an abrasive material dispersed in a solvent and potassium hydroxide (KOH) to the polishing system, wherein the slurry has a pH of about 10 or greater; and

polishing the organosilicate layer using the slurry.

20. (Canceled)

21. (Original) The method of claim 19 wherein the abrasive material has an average particle size greater than about 35 nm (nanometers).

22-24. (Canceled)

25. (Previously Presented) The method of claim 19 wherein the concentration of abrasive material in the slurry is within a range of about 22% by weight to about 30% by weight.

26. (Original) The method of claim 19 wherein the organosilicate layer is polished by placing it in contact with a polishing pad having the slurry thereon, and wherein the polishing pad is disposed upon a rotatable platen.

27. (Original) The method of claim 26 wherein the polishing pad comprises polyurethane.

28. (Original) The method of claim 26 wherein the organosilicate layer contacts the polishing pad with a pressure within a range of about 1 psi (pounds/square inch) to about 4 psi.

29. (Original) The method of claim 26 wherein the platen rotates at a speed within a range of about 0.1 m/s (meters/second) to about 2.0 m/s.

30. (Previously Presented) A method for planarizing an organosilicate layer, comprising:

positioning a substrate having an organosilicate layer thereon in a polishing system;

providing a slurry including silica as an abrasive material having an average particle size greater than about 35 nm and dispersed in a solvent and potassium hydroxide (KOH) or ammonium hydroxide (NH_4OH) to the polishing system, wherein the slurry has a pH of about 10 or greater and the concentration of the abrasive material in the slurry is within a range of about 22% by weight to about 30% by weight;

and polishing the organosilicate layer using the slurry.

31-34. (Canceled)

35. (Previously Presented) The method of claim 30, wherein the organosilicate layer is polished by placing it in contact with a polishing pad, the polishing pad having the slurry thereon, and wherein the polishing pad is disposed upon a rotatable platen.

36. (Currently Amended) The method of claim 35, wherein the organosilicate layer contacts the polishing pad with a pressure within a range of about 1 psi (pounds/square inch) to about 14 psi.